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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of **Embedded - Microprocessors**

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

E·XFI

Product Status	Active
Core Processor	PowerPC e600
Number of Cores/Bus Width	2 Core, 32-Bit
Speed	1.333GHz
Co-Processors/DSP	
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	
Ethernet	10/100/1000Mbps (4)
SATA	
USB	-
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	· · · · · · · · · · · · · · · · · · ·
Package / Case	1023-BCBGA, FCCBGA
Supplier Device Package	1023-FCCBGA (33x33)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mc8641dthx1333je

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Electrical Characteristics

Figure 2 shows the undershoot and overshoot voltages at the interfaces of the MPC8641.



Figure 2. Overshoot/Undershoot Voltage for Dn_M/O/L/TV_{IN}

The MPC8641 core voltage must always be provided at nominal V_{DD} _Core*n* (See Table 2 for actual recommended core voltage). Voltage to the processor interface I/Os are provided through separate sets of supply pins and must be provided at the voltages shown in Table 2. The input voltage threshold scales with respect to the associated I/O supply voltage. OV_{DD} and L/TV_{DD} based receivers are simple CMOS I/O circuits and satisfy appropriate LVCMOS type specifications. The DDR SDRAM interface uses a single-ended differential receiver referenced to each externally supplied Dn_MV_{REF} signal (nominally set to $Dn_GV_{DD}/2$) as is appropriate for the (SSTL-18 and SSTL-25) electrical signaling standards.



Input Clocks

should meet the MPC8641 input cycle-to-cycle jitter requirement. Frequency modulation and spread are separate concerns, and the MPC8641 is compatible with spread spectrum sources if the recommendations listed in Table 9 are observed.

Table 9. Spread Spectrum Clock Source Recommendations

At recommended operating conditions. See Table 2.

Parameter	Min	Мах	Unit	Notes
Frequency modulation	—	50	kHz	1
Frequency spread		1.0	%	1, 2

Notes:

1. Guaranteed by design.

2. SYSCLK frequencies resulting from frequency spreading, and the resulting core and VCO frequencies, must meet the minimum and maximum specifications given in Table 8.

It is imperative to note that the processor's minimum and maximum SYSCLK, core, and VCO frequencies must not be exceeded regardless of the type of clock source. Therefore, systems in which the processor is operated at its maximum rated e600 core frequency should avoid violating the stated limits by using down-spreading only.

 SDn_REF_CLK and $\overline{SDn_REF_CLK}$ was designed to work with a spread spectrum clock (+0 to 0.5% spreading at 30–33kHz rate is allowed), assuming both ends have same reference clock. For better results use a source without significant unintended modulation.

4.2 Real Time Clock Timing

The RTC input is sampled by the platform clock (MPX clock). The output of the sampling latch is then used as an input to the counters of the PIC. There is no jitter specification. The minimum pulse width of the RTC signal should be greater than 2x the period of the MPX clock. That is, minimum clock high time is $2 \times t_{MPX}$, and minimum clock low time is $2 \times t_{MPX}$. There is no minimum RTC frequency; RTC may be grounded if not needed.

4.3 eTSEC Gigabit Reference Clock Timing

Table 10 provides the eTSEC gigabit reference clocks (EC1_GTX_CLK125 and EC2_GTX_CLK125) AC timing specifications for the MPC8641.

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Notes
ECn_GTX_CLK125 frequency	f _{G125}	—	125 ±100 ppm	_	MHz	3
ECn_GTX_CLK125 cycle time	t _{G125}	—	8	_	ns	—
ECn_GTX_CLK125 peak-to-peak jitter	t _{G125J}	—		250	ps	1

Table 10. ECn_GTX_CLK125 AC Timing Specifications



DDR and DDR2 SDRAM

Figure 5 shows the DDR SDRAM output timing for the MCK to MDQS skew measurement (tDDKHMH).



Figure 5. Timing Diagram for tDDKHMH

Figure 6 shows the DDR SDRAM output timing diagram.



Figure 6. DDR SDRAM Output Timing Diagram



Ethernet: Enhanced Three-Speed Ethernet (eTSEC), MII Management

8.2.3.2 MII Receive AC Timing Specifications

Table 31 provides the MII receive AC timing specifications.

Table 31. MII Receive AC Timing Specifications

At recommended operating conditions with L/TV_{DD} of 3.3 V \pm 5%.

Parameter/Condition	Symbol ¹	Min	Тур	Мах	Unit
RX_CLK clock period 10 Mbps	t _{MRX} 2,3	—	400	—	ns
RX_CLK clock period 100 Mbps	t _{MRX} ³	—	40	—	ns
RX_CLK duty cycle	t _{MRXH} /t _{MRX}	35	—	65	%
RXD[3:0], RX_DV, RX_ER setup time to RX_CLK	t _{MRDVKH}	10.0	—	—	ns
RXD[3:0], RX_DV, RX_ER hold time to RX_CLK	t _{MRDXKH}	10.0	—	—	ns
RX_CLK clock rise time (20%-80%)	t _{MRXR} 2	1.0	—	4.0	ns
RX_CLK clock fall time (80%-20%)	t _{MRXF} 2	1.0	—	4.0	ns

Note:

1. The symbols used for timing specifications herein follow the pattern of t_{(first two letters of functional block)(signal)(state) (reference)(state)} for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{MRDVKH} symbolizes MII receive timing (MR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MRX} clock reference (K) going to the high (H) state or setup time. Also, t_{MRDXKL} symbolizes MII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{MRX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{MRX} represents the MII (M) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

2. Guaranteed by design.

3. ±100 ppm tolerance on RX_CLK frequency

Figure 14 provides the AC test load for eTSEC.



Figure 14. eTSEC AC Test Load

Figure 15 shows the MII receive AC timing diagram.



Figure 15. MII Receive AC Timing Diagram



Ethernet: Enhanced Three-Speed Ethernet (eTSEC), MII Management

Table 35. RGMII and RTBI AC Timing Specifications (continued)

At recommended operating conditions with L/TV_{DD} of 2.5 V \pm 5%.

Parameter/Condition	Symbol ¹	Min	Тур	Мах	Unit
Clock period duration ³	t _{RGT} ^{5,6}	7.2	8.0	8.8	ns
Duty cycle for 10BASE-T and 100BASE-TX $^{3, 4}$	t _{RGTH} /t _{RGT} 5	40	50	60	%
Rise time (20%–80%)	t _{RGTR} 5	—	-	0.75	ns
Fall time (80%-20%)	t _{RGTF} 5	—		0.75	ns

Notes:

1. Note that, in general, the clock reference symbol representation for this section is based on the symbols RGT to represent RGMII and RTBI timing. For example, the subscript of t_{RGT} represents the TBI (T) receive (RX) clock. Note also that the notation for rise (R) and fall (F) times follows the clock symbol that is being represented. For symbols representing skews, the subscript is skew (SK) followed by the clock that is being skewed (RGT).

- 2. This implies that PC board design will require clocks to be routed such that an additional trace delay of greater than 1.5 ns will be added to the associated clock signal.
- 3. For 10 and 100 Mbps, t_{RGT} scales to 400 ns ± 40 ns and 40 ns ± 4 ns, respectively.
- 4. Duty cycle may be stretched/shrunk during speed changes or while transitioning to a received packet's clock domains as long as the minimum duty cycle is not violated and stretching occurs for no more than three t_{RGT} of the lowest speed transitioned between.
- 5. Guaranteed by characterization
- 6. ±100 ppm tolerance on RX_CLK frequency

Figure 19 shows the RGMII and RTBI AC timing and multiplexing diagrams.



Figure 19. RGMII and RTBI AC Timing and Multiplexing Diagrams



Figure 26 to Figure 31 show the local bus signals.



Figure 26. Local Bus Signals (PLL Enabled)

NOTE

PLL bypass mode is recommended when LBIU frequency is at or below 83 MHz. When LBIU operates above 83 MHz, LBIU PLL is recommended to be enabled.

Table 42 describes the general timing parameters of the local bus interface at $OV_{DD} = 3.3$ V with PLL bypassed.

Table 42. Local Bus	Timing Parameters—F	LL Bypassed
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Parameter	Symbol ¹	Min	Мах	Unit	Notes
Local bus cycle time	t _{LBK}	12	_	ns	2
Local bus duty cycle	t _{LBKH/} t _{LBK}	45	55	%	—
Internal launch/capture clock to LCLK delay	t _{LBKHKT}	2.3	3.9	ns	8
Input setup to local bus clock (except LGTA/LUPWAIT)	t _{LBIVKH1}	5.7	_	ns	4, 5
LGTA/LUPWAIT input setup to local bus clock	t _{LBIVKL2}	5.6	_	ns	4, 5
Input hold from local bus clock (except LGTA/LUPWAIT)	t _{LBIXKH1}	-1.8	_	ns	4, 5

Parameter	Symbol ¹	Min	Мах	Unit	Notes
LGTA/LUPWAIT input hold from local bus clock	t _{LBIXKL2}	-1.3	—	ns	4, 5
LALE output transition to LAD/LDP output transition (LATCH hold time)	t _{LBOTOT}	1.5	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	t _{LBKLOV1}		-0.3	ns	
Local bus clock to data valid for LAD/LDP	t _{LBKLOV2}		-0.1	ns	4
Local bus clock to address valid for LAD	t _{LBKLOV3}	_	0	ns	4
Local bus clock to LALE assertion	t _{LBKLOV4}		0	ns	4
Output hold from local bus clock (except LAD/LDP and LALE)	t _{LBKLOX1}	-3.2	—	ns	4
Output hold from local bus clock for LAD/LDP	t _{LBKLOX2}	-3.2	—	ns	4
Local bus clock to output high Impedance (except LAD/LDP and LALE)	t _{lbkloz1}	_	0.2	ns	7
Local bus clock to output high impedance for LAD/LDP	t _{LBKLOZ2}	_	0.2	ns	7

Table 42. Local Bus Timing Parameters—PLL Bypassed (continued)

Notes:

The symbols used for timing specifications herein follow the pattern of t<sub>(First two letters of functional block)(signal)(state) (reference)(state) for inputs and t_{(First two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{LBIXKH1} symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one(1). Also, t_{LBKH0X} symbolizes local bus timing (LB) for the output (O) going invalid (X) or output hold time.
</sub>

 All timings are in reference to local bus clock for PLL bypass mode. Timings may be negative with respect to the local bus clock because the actual launch and capture of signals is done with the internal launch/capture clock, which precedes LCLK by t_{LBKHKT}.

 Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[n]. Skew measured between complementary signals at BV_{DD}/2.

4. All signals are measured from BVDD/2 of the rising edge of local bus clock for PLL bypass mode to 0.4 x BVDD of the signal in question for 3.3-V signaling levels.

- 5. Input timings are measured at the pin.
- 6. The value of t_{LBOTOT} is the measurement of the minimum time between the negation of LALE and any change in LAD

7. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.

8. Guaranteed by characterization.



Figure 34 provides the $\overline{\text{TRST}}$ timing diagram.



Figure 35 provides the boundary-scan timing diagram.



Figure 35. Boundary-Scan Timing Diagram

12 I²C

This section describes the DC and AC electrical characteristics for the I²C interfaces of the MPC8641.

12.1 I²C DC Electrical Characteristics

Table 45 provides the DC electrical characteristics for the I²C interfaces.

Table 45. I²C DC Electrical Characteristics

At recommended operating conditions with OV_{DD} of 3.3 V ± 5%.

Parameter	Symbol	Min	Мах	Unit	Notes
Input high voltage level	V _{IH}	$0.7 \times \text{OV}_{\text{DD}}$	OV _{DD} + 0.3	V	_
Input low voltage level	V _{IL}	-0.3	$0.3 \times OV_{DD}$	V	_
Low level output voltage	V _{OL}	0	$0.2 \times OV_{DD}$	V	1
Pulse width of spikes which must be suppressed by the input filter	t _{I2KHKL}	0	50	ns	2
Input current each I/O pin (input voltage is between $0.1 \times OV_{DD}$ and $0.9 \times OV_{DD}$ (max)	I	-10	10	μA	3



Table 45. I²C DC Electrical Characteristics (continued)

At recommended operating conditions with OV_{DD} of 3.3 V ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
Capacitance for each I/O pin	CI	_	10	pF	

Notes:

1. Output voltage (open drain or open collector) condition = 3 mA sink current.

2. Refer to the MPC8641 Integrated Host Processor Reference Manual for information on the digital filter used.

3. I/O pins will obstruct the SDA and SCL lines if $\ensuremath{\mathsf{OV}_{\mathsf{DD}}}$ is switched off.

12.2 I²C AC Electrical Specifications

Table 46 provides the AC timing parameters for the I^2C interfaces.

Table 46. I²C AC Electrical Specifications

All values refer to V_{IH} (min) and V_{IL} (max) levels (see Table 45).

Parameter	Symbol ¹	Min	Мах	Unit
SCL clock frequency	f _{I2C}	0	400	kHz
Low period of the SCL clock	t _{I2CL} 4	1.3	—	μS
High period of the SCL clock	t _{I2CH} 4	0.6	—	μS
Setup time for a repeated START condition	t _{I2SVKH} 4	0.6	—	μS
Hold time (repeated) START condition (after this period, the first clock pulse is generated)	t _{I2SXKL} 4	0.6	—	μS
Data setup time	t _{I2DVKH} 4	100	_	ns
Data input hold time: CBUS compatible masters I ² C bus devices	t _{i2DXKL}	0 ²	_	μs
Rise time of both SDA and SCL signals	t _{I2CR}	20 + 0.1 C _B ⁵	300	ns
Fall time of both SDA and SCL signals	t _{I2CF}	20 + 0.1 C _b ⁵	300	ns
Data output delay time	t _{I2OVKL}	—	0.9 ³	μS
Set-up time for STOP condition	^t I2PVKH	0.6	—	μS
Bus free time between a STOP and START condition	t _{I2KHDX}	1.3	—	μS
Noise margin at the LOW level for each connected device (including hysteresis)	V _{NL}	$0.1 \times OV_{DD}$	_	V

High-Speed Serial Interfaces (HSSI)

The Differential Input Voltage (or Swing) of the receiver, V_{ID} , is defined as the difference of the two complimentary input voltages: $V_{SDn_RX} - V_{\overline{SDn_RX}}$. The V_{ID} value can be either positive or negative.

4. Differential Peak Voltage, VDIFFp

The peak value of the differential transmitter output signal or the differential receiver input signal is defined as Differential Peak Voltage, $V_{DIFFp} = |A - B|$ Volts.

5. Differential Peak-to-Peak, VDIFFp-p

Since the differential output signal of the transmitter and the differential input signal of the receiver each range from A – B to –(A – B) Volts, the peak-to-peak value of the differential transmitter output signal or the differential receiver input signal is defined as Differential Peak-to-Peak Voltage, $V_{DIFFp-p} = 2*V_{DIFFp} = 2*|(A – B)|$ Volts, which is twice of differential swing in amplitude, or twice of the differential peak. For example, the output differential peak-peak voltage can also be calculated as $V_{TX-DIFFp-p} = 2*|V_{OD}|$.

6. Differential Waveform

The differential waveform is constructed by subtracting the inverting signal ($\overline{\text{SD}n_{TX}}$, for example) from the non-inverting signal ($\overline{\text{SD}n_{TX}}$, for example) within a differential pair. There is only one signal trace curve in a differential waveform. The voltage represented in the differential waveform is not referenced to ground. Refer to Figure 47 as an example for differential waveform.

7. Common Mode Voltage, V_{cm}

The Common Mode Voltage is equal to one half of the sum of the voltages between each conductor of a balanced interchange circuit and ground. In this example, for SerDes output, $V_{cm_out} = (V_{SDn_TX} + V_{\overline{SDn_TX}})/2 = (A + B) / 2$, which is the arithmetic mean of the two complimentary output voltages within a differential pair. In a system, the common mode voltage may often differ from one component's output to the other's input. Sometimes, it may be even different between the receiver input and driver output circuits within the same component. It is also referred as the DC offset in some occasion.



Figure 38. Differential Voltage Definitions for Transmitter or Receiver



15.4 Equalization

With the use of high speed serial links, the interconnect media will cause degradation of the signal at the receiver. Effects such as Inter-Symbol Interference (ISI) or data dependent jitter are produced. This loss can be large enough to degrade the eye opening at the receiver beyond what is allowed in the specification. To negate a portion of these effects, equalization can be used. The most common equalization techniques that can be used are:

- A passive high pass filter network placed at the receiver. This is often referred to as passive equalization.
- The use of active circuits in the receiver. This is often referred to as adaptive equalization.

15.5 Explanatory Note on Transmitter and Receiver Specifications

AC electrical specifications are given for transmitter and receiver. Long run and short run interfaces at three baud rates (a total of six cases) are described.

The parameters for the AC electrical specifications are guided by the XAUI electrical interface specified in Clause 47 of IEEE 802.3ae-2002.

XAUI has similar application goals to serial RapidIO, as described in Section 8.1. The goal of this standard is that electrical designs for serial RapidIO can reuse electrical designs for XAUI, suitably modified for applications at the baud intervals and reaches described herein.

15.6 Transmitter Specifications

LP-Serial transmitter electrical and timing specifications are stated in the text and tables of this section.

The differential return loss, S11, of the transmitter in each case shall be better than

- -10 dB for (Baud Frequency)/10 < Freq(f) < 625 MHz, and
- $-10 \text{ dB} + 10\log(f/625 \text{ MHz}) \text{ dB}$ for $625 \text{ MHz} \le \text{Freq}(f) \le \text{Baud}$ Frequency

The reference impedance for the differential return loss measurements is 100 Ohm resistive. Differential return loss includes contributions from on-chip circuitry, chip packaging and any off-chip components related to the driver. The output impedance requirement applies to all valid output levels.

It is recommended that the 20%–80% rise/fall time of the transmitter, as measured at the transmitter output, in each case have a minimum value 60 ps.

It is recommended that the timing skew at the output of an LP-Serial transmitter between the two signals that comprise a differential pair not exceed 25 ps at 1.25 GB, 20 ps at 2.50 GB and 15 ps at 3.125 GB.



Characteristic	Symbol	Ra	nge	Unit	Notes
Characteristic	Symbol	Min	Мах	Onit	Notes
Output Voltage,	Vo	-0.40	2.30	Volts	Voltage relative to COMMON of either signal comprising a differential pair
Differential Output Voltage	V _{DIFFPP}	800	1600	mV p-p	_
Deterministic Jitter	J _D	—	0.17	UI p-p	—
Total Jitter	J _T	—	0.35	UI p-p	—
Multiple output skew	S _{MO}	_	1000	ps	Skew at the transmitter output between lanes of a multilane link
Unit Interval	UI	320	320	ps	+/– 100 ppm

For each baud rate at which an LP-Serial transmitter is specified to operate, the output eye pattern of the transmitter shall fall entirely within the unshaded portion of the Transmitter Output Compliance Mask shown in Figure 54 with the parameters specified in Table 58 when measured at the output pins of the device and the device is driving a $100 \Omega + -5\%$ differential resistive load. The output eye pattern of an LP-Serial transmitter that implements pre-emphasis (to equalize the link and reduce inter-symbol interference) need only comply with the Transmitter Output Compliance Mask when pre-emphasis is disabled or minimized.







Transmitter Type	V _{DIFF} min (mV)	V _{DIFF} max (mV)	A (UI)	B (UI)
1.25 GBaud short range	250	500	0.175	0.39
1.25 GBaud long range	400	800	0.175	0.39
2.5 GBaud short range	250	500	0.175	0.39
2.5 GBaud long range	400	800	0.175	0.39
3.125 GBaud short range	250	500	0.175	0.39
3.125 GBaud long range	400	800	0.175	0.39

Table 58. Transmitter Differential Output Eye Diagram Parameters

15.7 Receiver Specifications

LP-Serial receiver electrical and timing specifications are stated in the text and tables of this section.

Receiver input impedance shall result in a differential return loss better that 10 dB and a common mode return loss better than 6 dB from 100 MHz to (0.8)*(Baud Frequency). This includes contributions from on-chip circuitry, the chip package and any off-chip components related to the receiver. AC coupling components are included in this requirement. The reference impedance for return loss measurements is 100 Ohm resistive for differential return loss and 25 Ohm resistive for common mode.

Characteristic	Symbol	Range		Unit	Notos	
Characteristic	Symbol	Min	Мах	Unit	Notes	
Differential Input Voltage	V _{IN}	200	1600	mV p-p	Measured at receiver	
Deterministic Jitter Tolerance	J _D	0.37	—	UI p-p	Measured at receiver	
Combined Deterministic and Random Jitter Tolerance	J _{DR}	0.55	_	UI p-p	Measured at receiver	
Total Jitter Tolerance ¹	J _T	0.65	—	UI p-p	Measured at receiver	
Multiple Input Skew	S _{MI}	—	24	ns	Skew at the receiver input between lanes of a multilane link	
Bit Error Rate	BER	—	10 ⁻¹²	—	—	
Unit Interval	UI	800	800	ps	+/- 100 ppm	

Table 59. Receiver AC Timing Specifications—1.25 GBaud

Note:

1. Total jitter is composed of three components, deterministic jitter, random jitter and single frequency sinusoidal jitter. The sinusoidal jitter may have any amplitude and frequency in the unshaded region of Figure 55. The sinusoidal jitter component is included to ensure margin for low frequency jitter, wander, noise, crosstalk and other variable system effects.



Serial RapidIO



Figure 56. Receiver Input Compliance Mask

Receiver Type	V _{DIFF} min (mV)	V _{DIFF} max (mV)	A (UI)	B (UI)
1.25 GBaud	100	800	0.275	0.400
2.5 GBaud	100	800	0.275	0.400
3.125 GBaud	100	800	0.275	0.400

Table 62. Receiver Input Compliance Mask Parameters Exclusive of Sinusoidal Jitter

15.9 Measurement and Test Requirements

Since the LP-Serial electrical specification are guided by the XAUI electrical interface specified in Clause 47 of IEEE 802.3ae-2002, the measurement and test requirements defined here are similarly guided by Clause 47. In addition, the CJPAT test pattern defined in Annex 48A of IEEE 802.3ae-2002 is specified as the test pattern for use in eye pattern and jitter measurements. Annex 48B of IEEE 802.3ae-2002 is recommended as a reference for additional information on jitter test methods.

15.9.1 Eye Template Measurements

For the purpose of eye template measurements, the effects of a single-pole high pass filter with a 3 dB point at (Baud Frequency)/1667 is applied to the jitter. The data pattern for template measurements is the



8. Note that for MPC8641 (single core) the solder balls for the following signals/pins are not populated in the package: VDD_Core1 (R16, R18, R20, T17, T19, T21, T23, U16, U18, U22, V17, V19, V21, V23, W16, W18, W20, W22, Y17, Y19, Y21, Y23, AA16, AA18, AA20, AA22, AB23, AC24) and SENSEVDD_Core1 (U20).





NOTES for Figure 58

- 1. All dimensions are in millimeters.
- 2. Dimensions and tolerances per ASME Y14.5M-1994.
- 3. Maximum solder ball diameter measured parallel to datum A.
- 4. Datum A, the seating plane, is defined by the spherical crowns of the solder balls.
- 5. Capacitors may not be present on all devices.
- 6. Caution must be taken not to short capacitors or expose metal capacitor pads on package top.
- 7. All dimensions symmetrical about centerlines unless otherwise specified.
- Note that for MPC8641 (single core) the solder balls for the following signals/pins are not populated in the package: VDD_Core1 (R16, R18, R20, T17, T19, T21, T23, U16, U18, U22, V17, V19, V21, V23, W16, W18, W20, W22, Y17, Y19, Y21, Y23, AA16, AA18, AA20, AA22, AB23, AC24) and SENSEVDD_Core1 (U20).





Figure 59. FC-CBGA Package Exploded Cross-Sectional View with Several Heat Sink Options

There are several commercially-available heat sinks for the MPC8641 provided by the following vendors:

Aavid Thermalloy 80 Commercial St. Concord, NH 03301 Internet: www.aavidthermalloy.com	603-224-9988		
Advanced Thermal Solutions 89 Access Road #27. Norwood, MA02062 Internet: www.qats.com	781-769-2800		
Alpha Novatech 473 Sapena Ct. #12 Santa Clara, CA 95054 Internet: www.alphanovatech.com	408-749-7601		
Calgreg Thermal Solutions 60 Alhambra Road, Suite 1 Warwick, RI 02886 Internet: www.calgreg.com	888-732-6100		
International Electronic Research Corporation (IERC)818-842-7277 413 North Moss St. Burbank, CA 91502 Internet: www.ctscorp.com			
Millennium Electronics (MEI) Loroco Sites 671 East Brokaw Road San Jose, CA 95112 Internet: www.mei-thermal.com	408-436-8770		



19.2.2 Thermal Interface Materials

A thermal interface material is recommended at the package-to-heat sink interface to minimize the thermal contact resistance. Figure 61 shows the thermal performance of three thin-sheet thermal-interface materials (silicone, graphite/oil, floroether oil), a bare joint, and a joint with thermal grease as a function of contact pressure. As shown, the performance of these thermal interface materials improves with increasing contact pressure. The use of thermal grease significantly reduces the interface thermal resistance. That is, the bare joint results in a thermal resistance approximately seven times greater than the thermal grease joint.

Often, heat sinks are attached to the package by means of a spring clip to holes in the printed-circuit board (see Figure 59). Therefore, synthetic grease offers the best thermal performance, considering the low interface pressure, and is recommended due to the high power dissipation of the MPC8641. Of course, the selection of any thermal interface material depends on many factors—thermal performance requirements, manufacturability, service temperature, dielectric properties, cost, and so on.



Figure 61. Thermal Performance of Select Thermal Interface Material

The board designer can choose between several types of thermal interface. Heat sink adhesive materials should be selected based on high conductivity and mechanical strength to meet equipment shock/vibration requirements. There are several commercially available thermal interfaces and adhesive materials provided by the following vendors:



The Bergquist Company 18930 West 78 th St. Chanhassen, MN 55317 Internet: www.bergquistcompany.com	800-347-4572
Chomerics, Inc. 77 Dragon Ct. Woburn, MA 01801 Internet: www.chomerics.com	781-935-4850
Dow-Corning Corporation Corporate Center PO Box 994 Midland, MI 48686-0994 Internet: www.dowcorning.com	800-248-2481
Shin-Etsu MicroSi, Inc. 10028 S. 51st St. Phoenix, AZ 85044 Internet: www.microsi.com	888-642-7674
Thermagon Inc. 4707 Detroit Ave. Cleveland, OH 44102 Internet: www.thermagon.com	888-246-9050

The following section provides a heat sink selection example using one of the commercially available heat sinks.

19.2.3 Heat Sink Selection Example

For preliminary heat sink sizing, the die-junction temperature can be expressed as follows:

 $T_j = T_i + T_r + (R_{\theta JC} + R_{\theta int} + R_{\theta sa}) \times P_d$

where:

T_i is the die-junction temperature

T_i is the inlet cabinet ambient temperature

 T_r is the air temperature rise within the computer cabinet

 $R_{\theta JC}$ is the junction-to-case thermal resistance

 $R_{\theta int}$ is the adhesive or interface material thermal resistance

 $R_{\theta sa}$ is the heat sink base-to-ambient thermal resistance

P_d is the power dissipated by the device

During operation, the die-junction temperatures (T_j) should be maintained less than the value specified in Table 2. The temperature of air cooling the component greatly depends on the ambient inlet air temperature and the air temperature rise within the electronic cabinet. An electronic cabinet inlet-air temperature (T_j) may range from 30° to 40°C. The air temperature rise within a cabinet (T_r) may be in the range of 5° to 10°C. The thermal resistance of the thermal interface material (R_{0int}) is typically about 0.2°C/W. For



Another useful equation is:

$$\mathbf{V}_{H} - \mathbf{V}_{L} = \mathbf{n} \frac{\mathbf{KT}}{\mathbf{q}} \left[\mathbf{In} \frac{\mathbf{I}_{H}}{\mathbf{I}_{L}} \right]$$

Where:

 $I_{fw} = Forward current$ $I_s = Saturation current$ $V_d = Voltage at diode$ $V_f = Voltage forward biased$ $V_H = Diode voltage while I_H is flowing$ $V_L = Diode voltage while I_L is flowing$ $I_H = Larger diode bias current$ $I_L = Smaller diode bias current$ $q = Charge of electron (1.6 \times 10^{-19} \text{ C})$ n = Ideality factor (normally 1.0) $K = Boltzman's constant (1.38 \times 10^{-23} \text{ Joules/K})$ T = Temperature (Kelvins)

The ratio of I_H to I_L is usually selected to be 10:1. The above simplifies to the following:

$$V_{H}-V_{L}=~1.986\times10^{-4}\times nT$$

Solving for T, the equation becomes:

$$\mathbf{nT} = \frac{\mathbf{V}_{\mathsf{H}} - \mathbf{V}_{\mathsf{L}}}{1.986 \times 10^{-4}}$$



Document Revision History

21.2 Part Marking

Parts are marked as the example shown in Figure 70.



NOTE: TWLYYWW is the test code MMMMMM is the M00 (mask) number. YWWLAZ is the assembly traceability code.

Figure 70. Part Marking for FC-CBGA Device

22 Document Revision History

Table 76 provides a revision history for the MPC8641D hardware specification.

Table 76. Document Revision History

Revision	Date	Substantive Change(s)
3	05/2014	 Updated the Serial RapidIO equation in Section 4.4, "Platform Frequency Requirements for PCI-Express and Serial RapidIO" Updated Section 19.2.4, "Temperature Diode," by removing the ideality factor value. Added VJ package type designator and footnotes to Table 74, "Part Numbering Nomenclature" and Section 16.1, "Package Parameters for the MPC8641."
2	07/2009	 Added note 8 to Table 49, "Differential Transmitter (TX) Output Specifications." Added Revision E to Table 74, "Part Numbering Nomenclature."
1	11/2008	 Added Section 4.4, "Platform Frequency Requirements for PCI-Express and Serial RapidIO." Removed the statement "Note that core processor speed of 1500 MHz is only available for the MPC8641D (dual core)" from Note 2 in Table 74 because a 1500 MHz core is offered for both MPC8641D (dual core) and MPC8641 (single core). Added Note 8 to Figure 57 and Figure 58.
0	07/2008	Initial Release